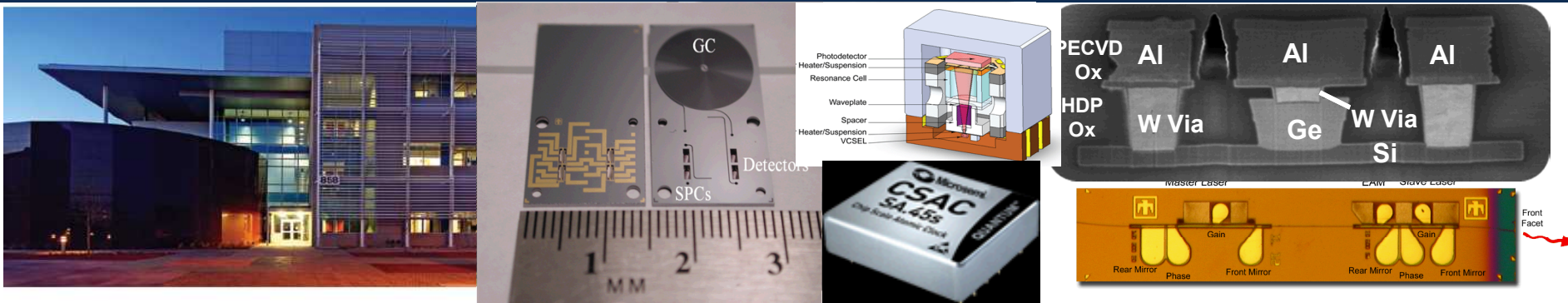


Exceptional service in the national interest



III-V's from Lab to Fab: Compound Semiconductor Devices and Integration Paths to Manufacturing

Greg Peake

Principal Member Technical Staff

gmpeake@sandia.gov

Exceptional service in the national interest



Introduction to Sandia National Laboratories and MESA

Foundational Technologies at MESA

Integration Challenges

Integration Paths

- Mechanical**
- Flip-Chip**
- Wafer Bonding**
- Direct Growth**
- Micromachining**

Working With Sandia

Microsystems and Engineering Sciences Applications (MESA): 400,000 Sq-ft Complex with >650 Employees in Secure Facility



MESA is an FFRDC-based development and production facility for any microsystem component or technology that cannot or should not be obtained commercially.

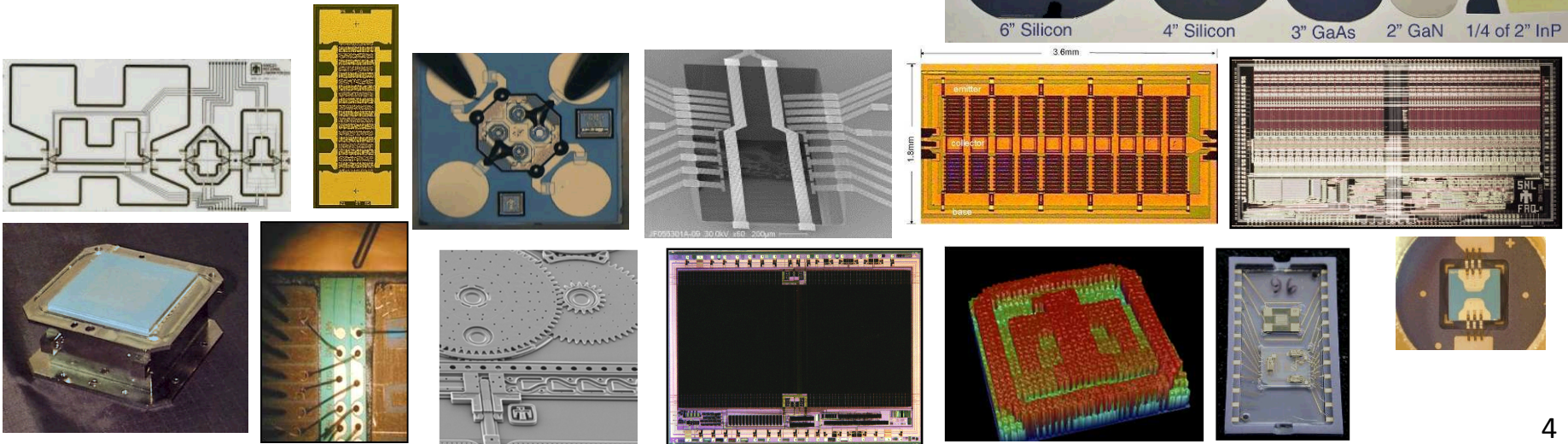
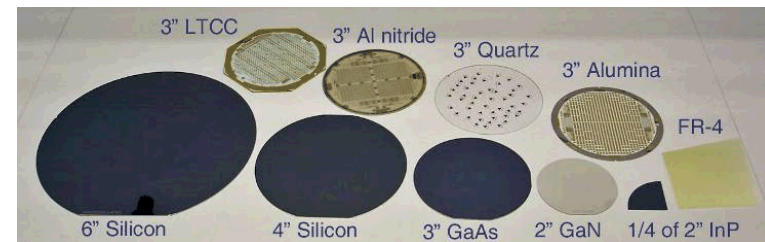
MESA Microfabrication Facilities

- MESA specializes in custom microelectronics, photonics, microtechnologies, and integrated systems
- NNSA's primary supplier of custom rad-hard ICs for weapon life extension programs and satellite systems
- Fast turn product capability: structured ASIC architecture
- Silicon bulk *and* silicon surface micromachining
- 6" silicon post-processing facility to support hybrid substrates and 3D integration (8" compatible)
- Compound semiconductor epitaxial growth
- Compound semiconductor discretes, IC's and MEMs
- Mixed-technology integration and processing
- Particularly suited to rapidly advance research concepts from TRL1-6 and deliver qualified products from TRL 7-9

SiFab: 33,000 ft² Class 1/10/100

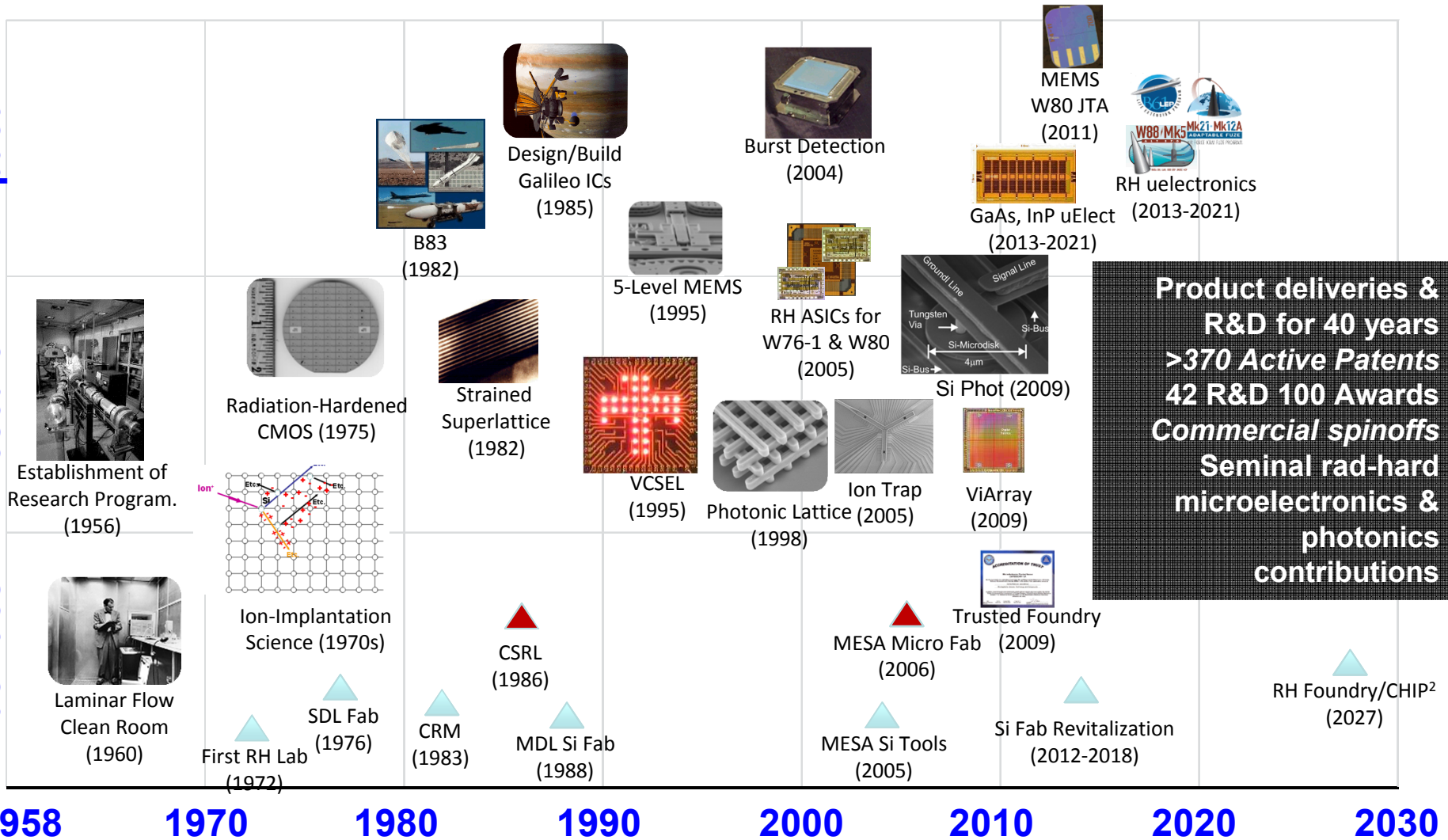


MicroFab: 16,600 ft² Class 10/100



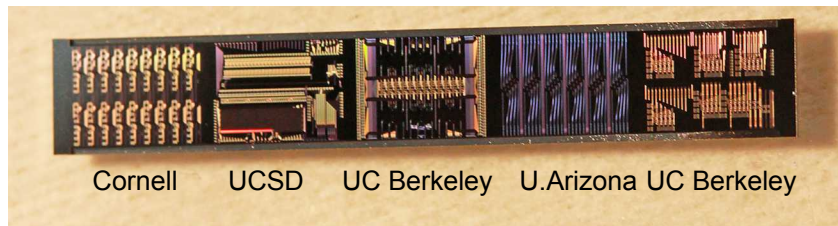
R&D enables and sustains Sandia's Radiation-Hardened Microelectronics/Microsystems Capability

Impact
Research
Facilities

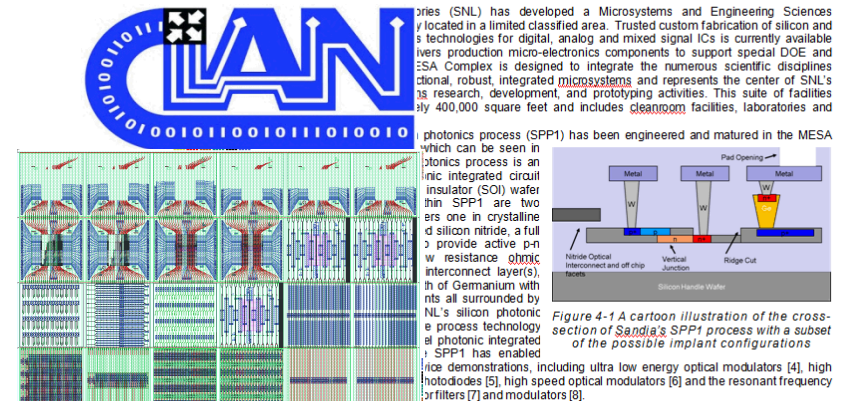


MISSION: Invent and mature integrated circuit and microsystems technologies that provide differentiation and impact for NW and other national security missions

- **SUMMIT V: 5 layer polysilicon MEMS process**
 - Developed design manual, DRC, many MPWs over the last decade
- **CMOS7 Electronics: Rad-hard, mixed-signal ASIC/ViaArray: 0.35 μ m, 3.3V core, 3.3V I/O, Cadence, MPWs since 2009**
- **SPP1 Silicon Photonics Process:**
 - 250nm Si/3000nm BOx
 - fJ/bit mods, 45 GHz dets, filters, etc.
 - SiN 2-layer guides/xovers
 - Design manual, initial DRC, pilot MPW runs

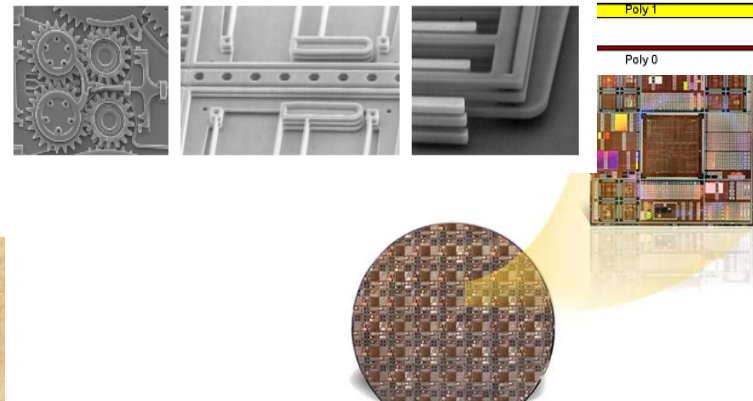
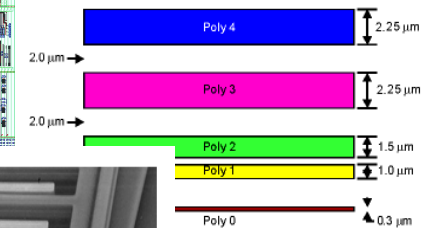


4. TECHNOLOGY OVERVIEW



SS DETAILS

Process flow of are described in Table 5-1. The base process can be broken



Trusted Advanced Pathfinder Products: Si Photonics

2014

balanced homodyne resonant wavelength stabilization > 55C

2013

Si Photonics MPW (CIAN NSF ERC)

2012

24 GHz Si TW MZM

2011

45 GHz Ge Detector

2010

3 fJ/bit resonator modulator, 1V-cm MZM

2009

wavelength tunable rings over 35 nm

2008

2.4 ns Wavelength selective switch

2007

MicroDisk resonator infrared detector

2005

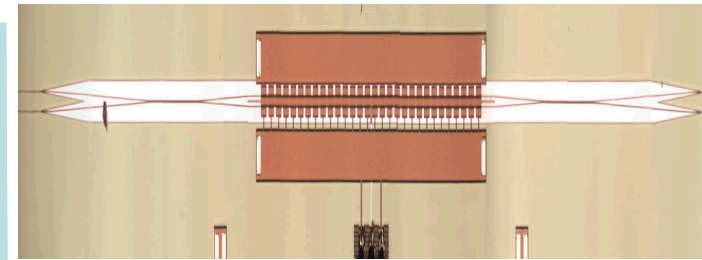
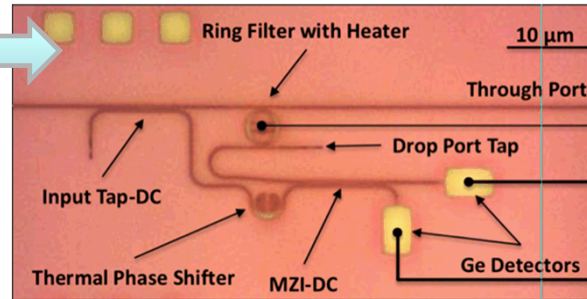
Si₃N₄ low-loss waveguides

2000

SiON / SiO₂ (Clarendon Photonics)

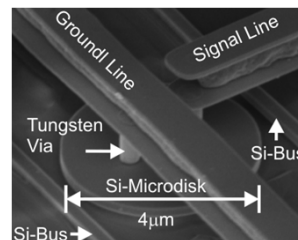
1990s

Si PhC & Optical MEMS

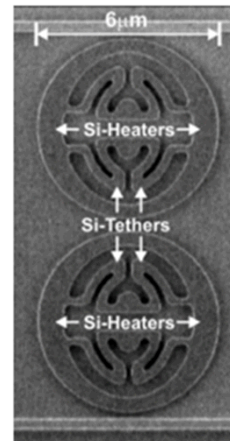


24 GHz 0.7V-cm Travelling Wave MZI Modulator

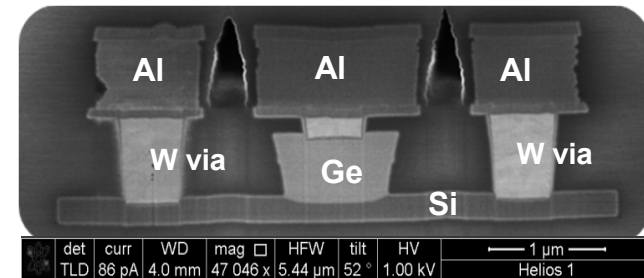
3.2fJ/bit at 12Gb/s



Resonant Optical Modulator/Filter

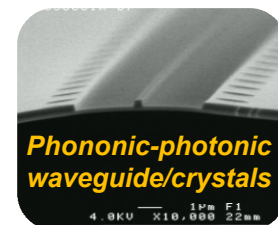


Tunable Resonant Filter



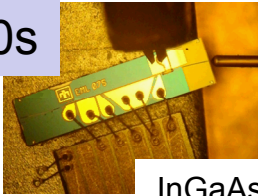
45 GHz High-speed Ge Detector on Si

MEMS process for additional capability

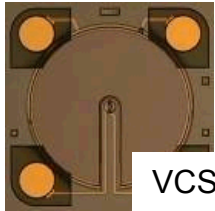


Trusted Advanced Pathfinder Products: III-V Photonics

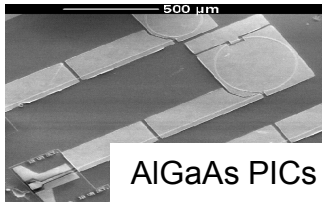
2010s



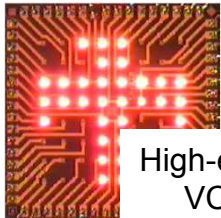
InGaAsP PICs



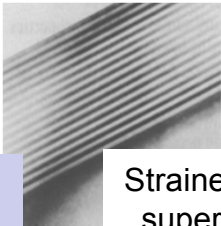
VCSEL+ PD



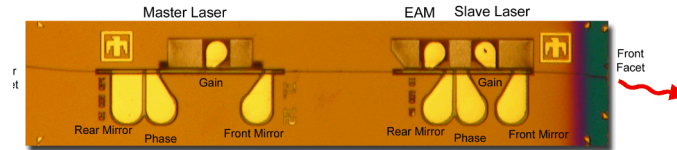
AlGaAs PICs



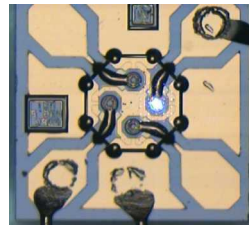
High-efficiency
VCSELs



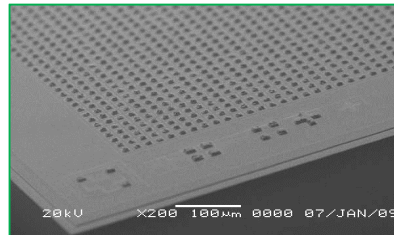
Strained-layer
superlattices



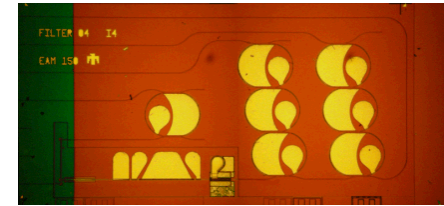
On-Chip Injection Locking
Enhanced Modulation > 50 GHz, C-Band



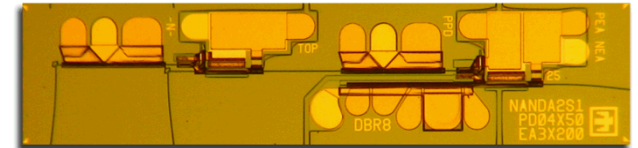
Single-Frequency Tunable VCSELs,
For atomic spectroscopy and sensors



nBn FPAs in the SWIR, MWIR and LWIR,
leveraging novel III-P and III-Sb materials



RF-Optical Channelizing Filter
1-20 GHz RF on C-Band Light

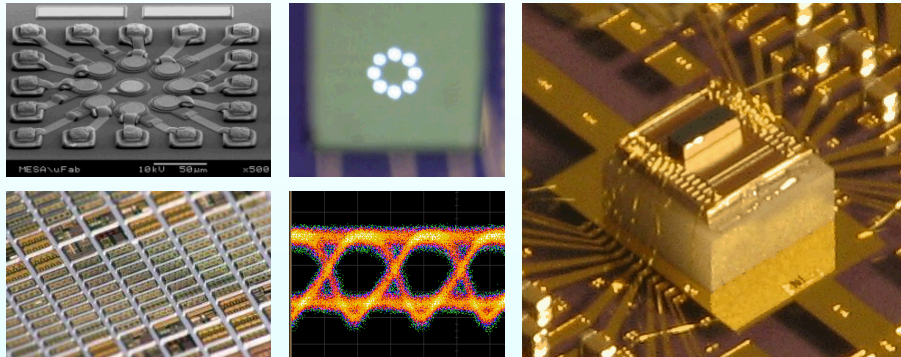


All-Optical Logic at >40 Gb/s, C-Band

- **Foundational Capabilities**
 - III-V compound semiconductor epitaxy, microfabrication, integration
 - Device physics, modeling, simulation
 - Microelectronics/optoelectronics, and complex mono/hetero-circuits
- **Prove, Advance Technology Readiness Level, Productize**
 - TRL1-6+: create, develop, prototype
 - NNSA QMS/QC-1-10; trusted
- **Trusted, low-volume, high-reliability products for harsh environments**

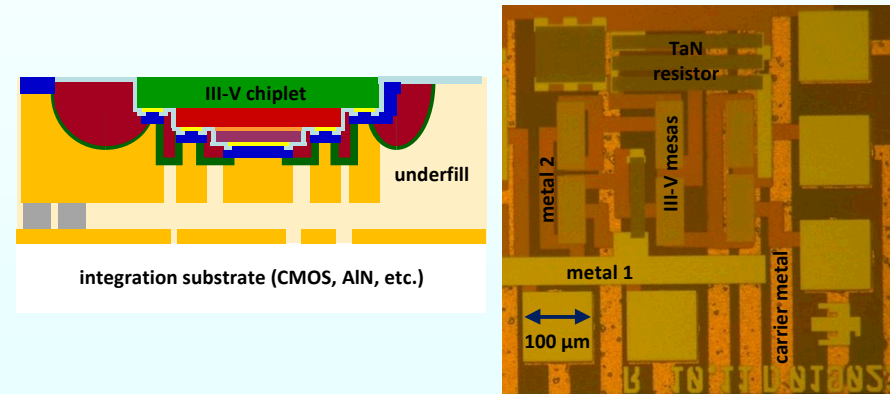
Trusted Advanced Pathfinder Products: Heterogeneous Integration

Optical Data Communications



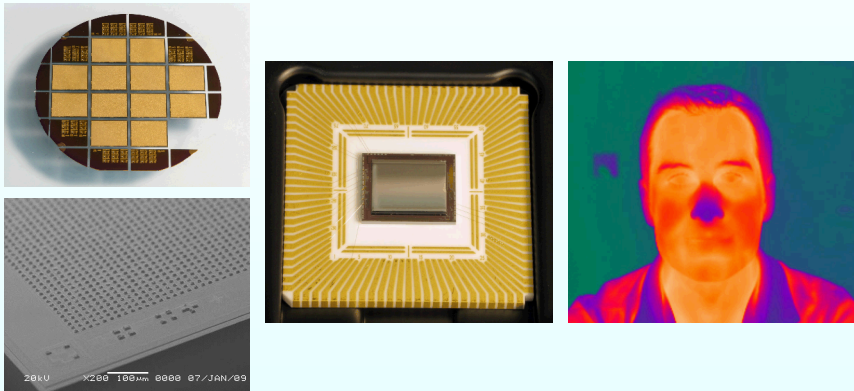
- GaAs- and InP-based devices: VCSELs, modulators, photodiodes
- dense integration onto 32-nm and 45-nm CMOS

Heterogeneous III-V/CMOS Microelectronics



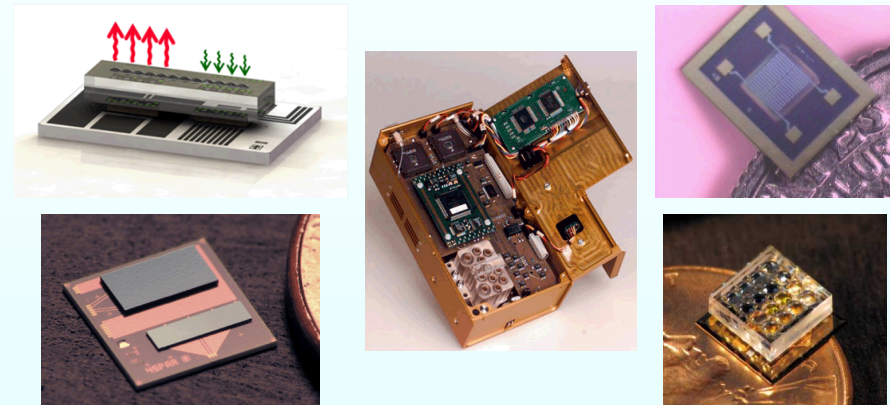
- complementary integration of GaAs and InP microelectronics
- III-V microelectronics circuitry on CMOS ASICs

IR Imagers for Remote Sensing



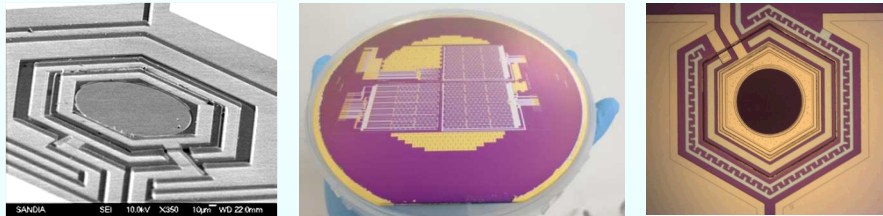
- nBn InAs/GaSb MWIR/LWIR detector arrays for large-format FPAs
- 10µm indium bump bonding, underfill, thinning, AR coating
- hybridization to silicon ROICs with >99.99% interconnect yield

Optical and MEMS-based Microsensors



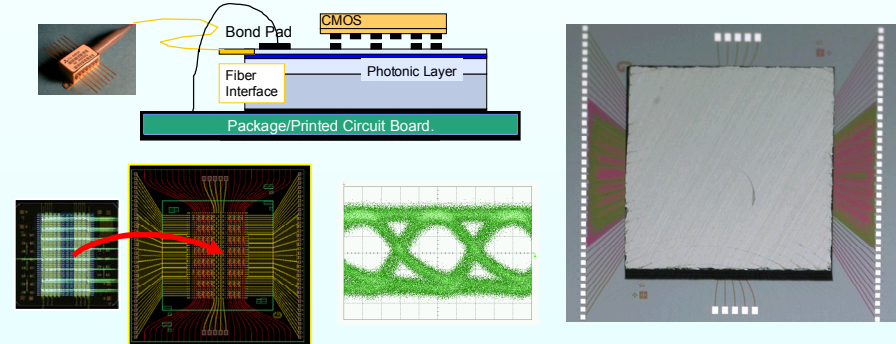
- chemical and bio sensors using MEMS and SAW devices
- g-hard optical microsensors with in-house photonics
- hybrid device integration with custom micro-optics

Microsystem-Enabled Photovoltaics



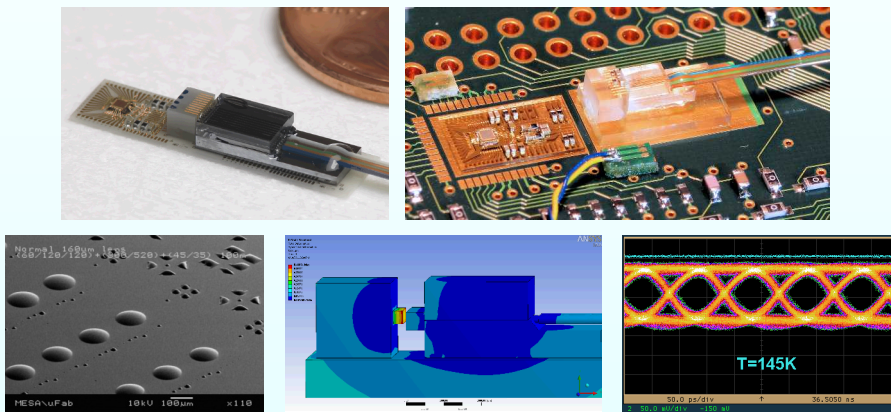
- wafer-level bonding for multi-junction solar cells
- InGaAsP/InP and InGaP/GaAs devices on silicon
- dielectric interfaces with III-V substrate removal
- integration with collection optics

High Performance Computing



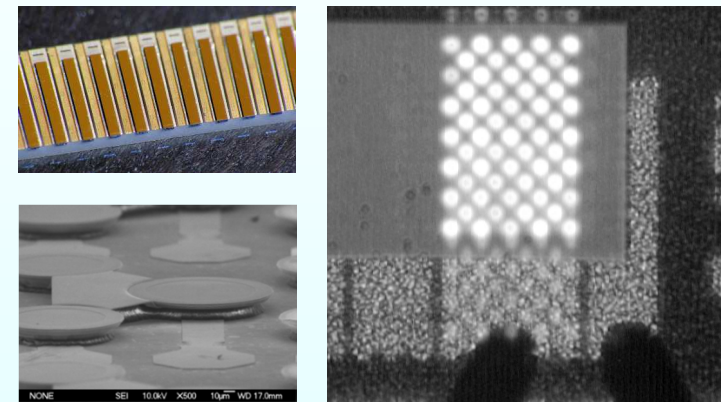
- silicon photonics on high-speed silicon ASIC
- independent optimization of electronics & photonics

Extreme Environment Applications



- custom photonics, optics, electronics for cryogenic interconnects
- advanced optoelectronics and integration for radiation hardness

High Performance Photonics



- high-power emitters on AlN and diamond
- RF packaging for high-speed test and measurement

How Can Sandia Help?

- **Expertise:** >30 years in III-V & Silicon Photonics R&D:
 - Toolboxes for internal and contract R&D
- **Capability:** Large flexible Si & III-V R&D Fab, Production rigor:
 - 65kft² fab, 10 epi reactors, >60 photonics staff, (60% Ph.D.)
 - Here today, here tomorrow...(NW IC deliveries)
 - Secure environment & staff, robust info-control (TRUST)
- **History of Technology Transfer to Industry:**



Processes

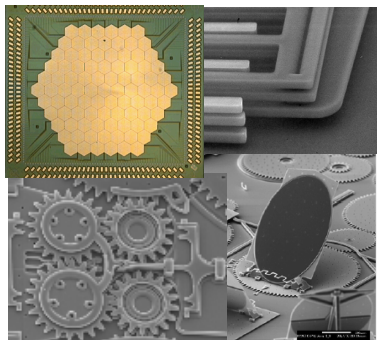
Devices

Subassemblies

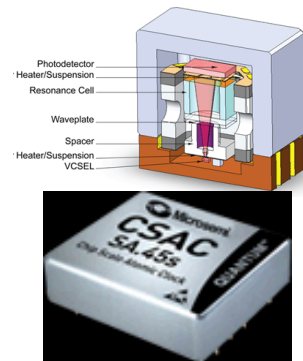
Systems

MEMS (Fairchild) VCSEL CSAC (Microsemi) POM (EMCORE) SAR (General Atomics)

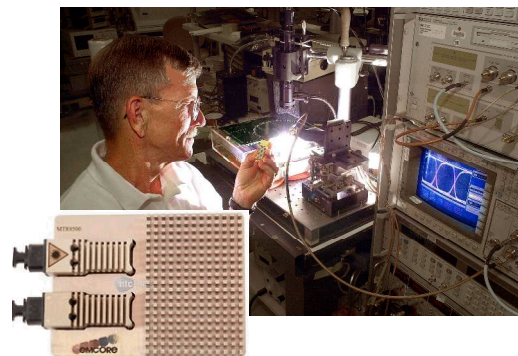
Transfer of Sandia's Summit IV™ MEMS technology. Network Photonics Optical MEMS



Narrow λ temp-stable VCSEL for Chip-scale Atomic Clock (DARPA)



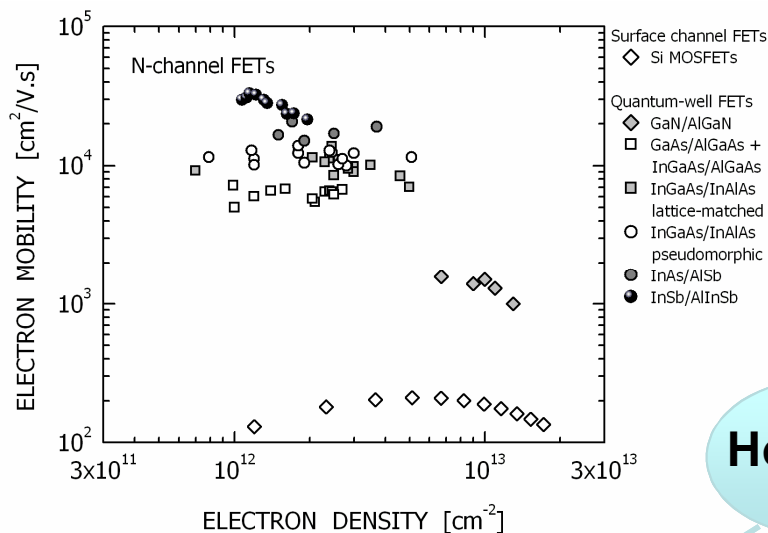
OC-192 Transponder Parallel Fiber Optic Module prototype development using VCSEL & PD arrays



Copperhead & Lynx SAR (w/ GA Aero) on TigerShark & Predator UAVs ([IED detector being transferred to Army](#))

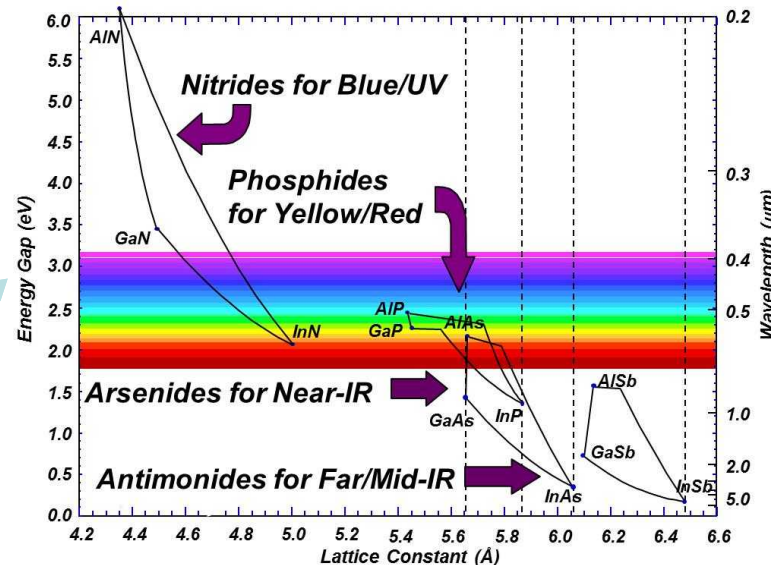


Superior Characteristics



However

Lattice Matching Challenges



ESH Challenges

Hazardous Production Materials

AsH_3 – 3 ppm IDLH

PH_3 – 50 ppm IDLH

$\text{III}(\text{CH}_3)_3$ are pyrophoric

H_2 carrier gas run at 24 lpm/Tool

And more...

Widely varying TCE

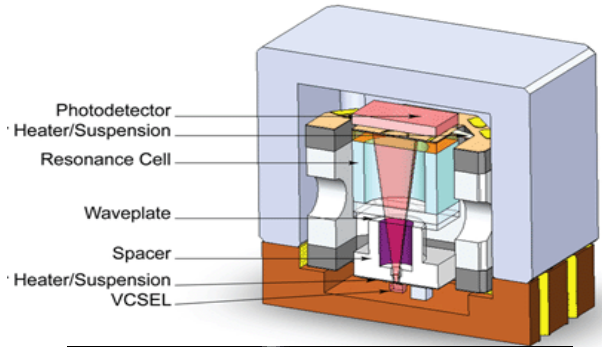
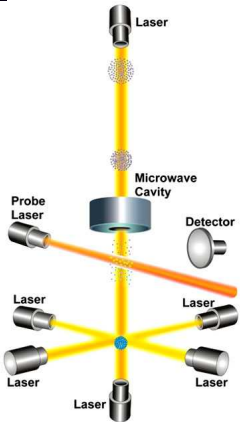
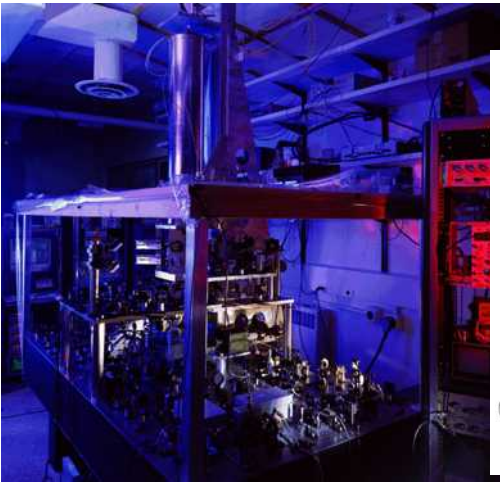
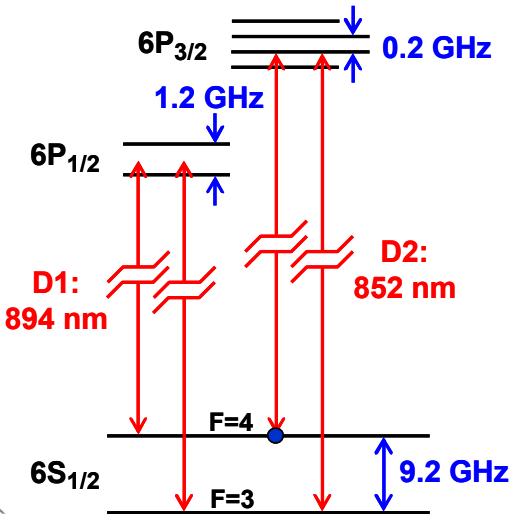
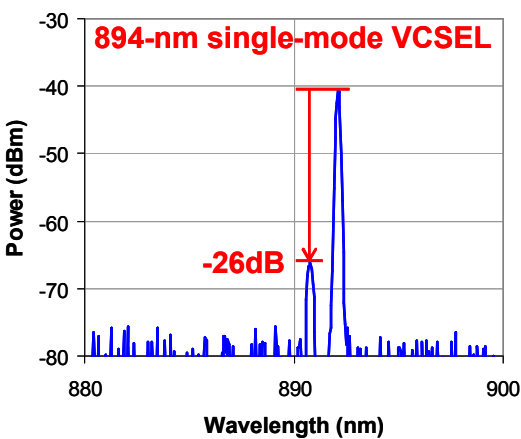
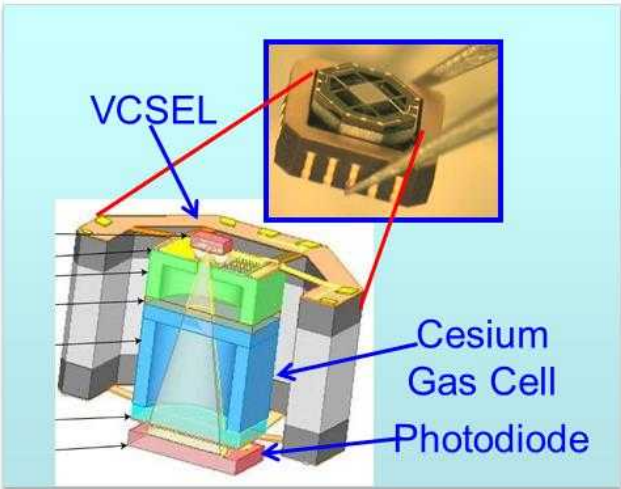
Directional Properties

Surface Termination is complex

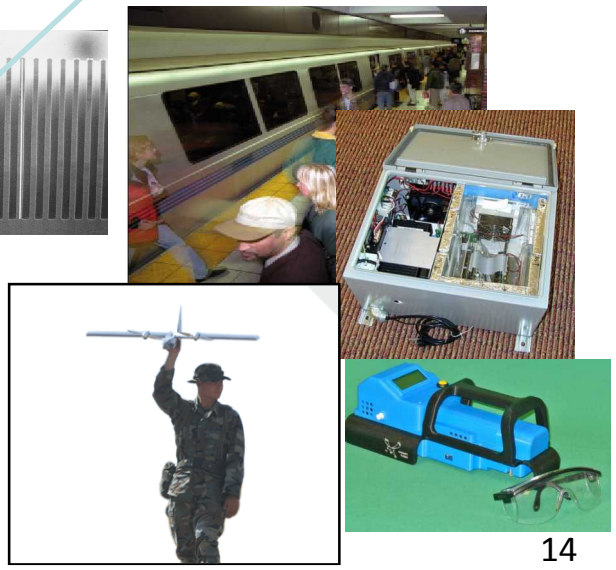
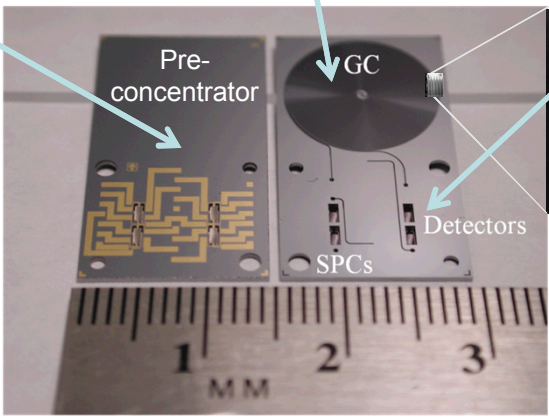
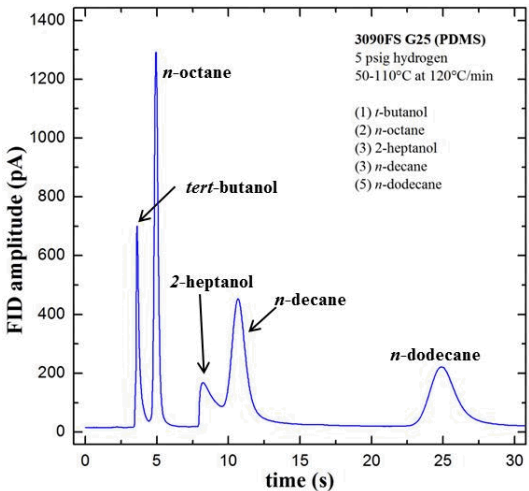
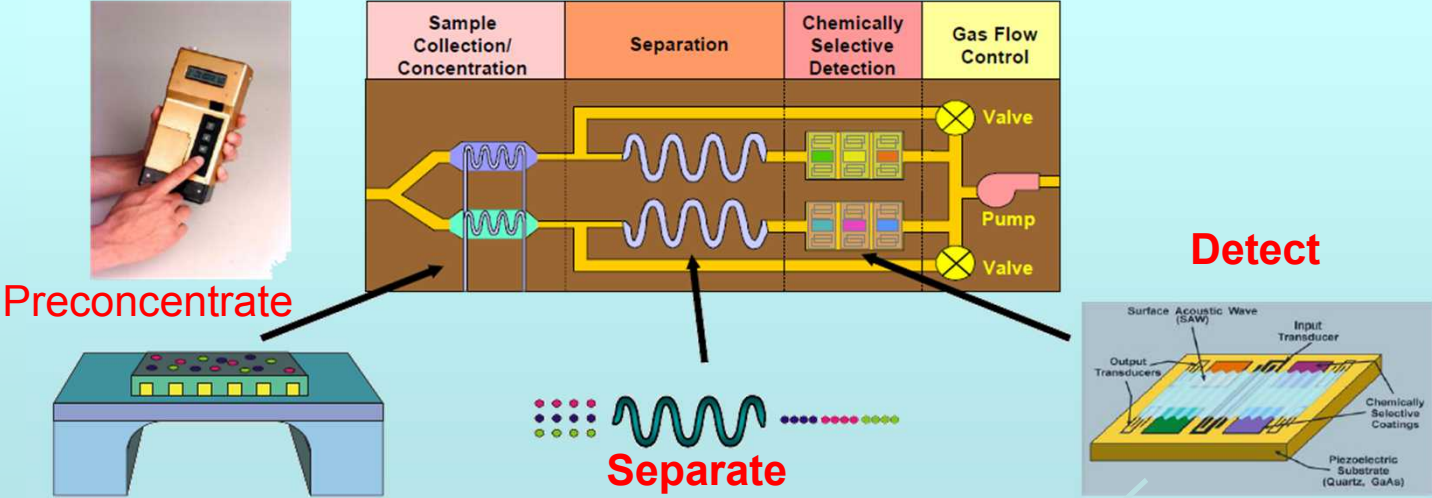
Heterogeneous interfaces must be understood

Etc...

Mechanical Integration – Chip Scale Atomic Clock

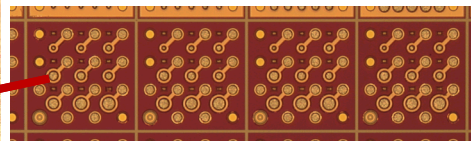
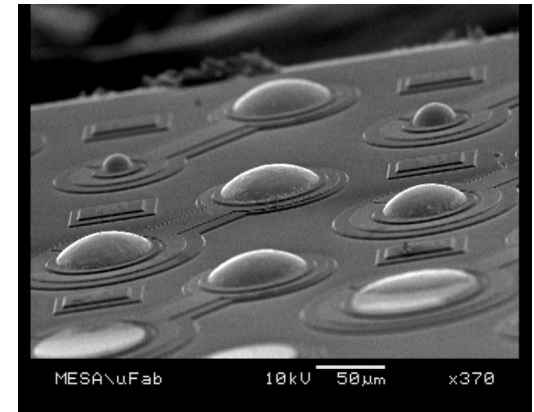
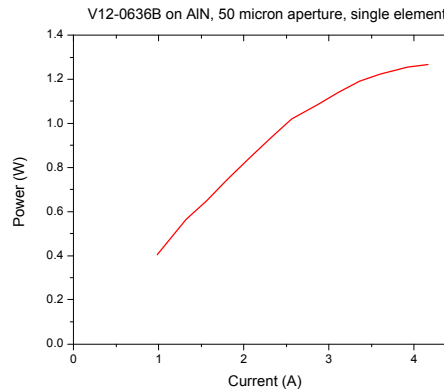
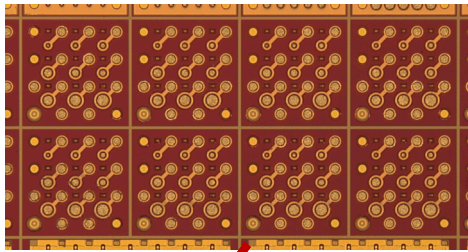


Unifying Concept of Operation

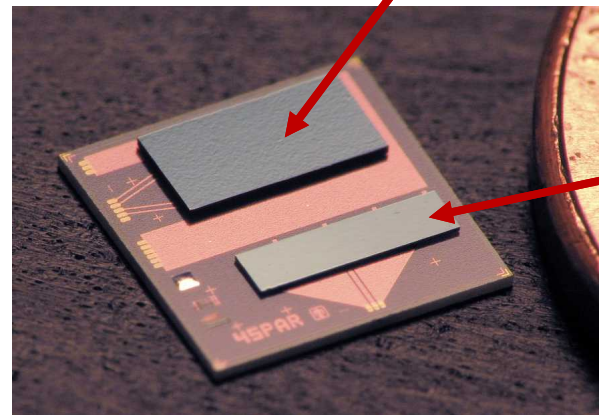
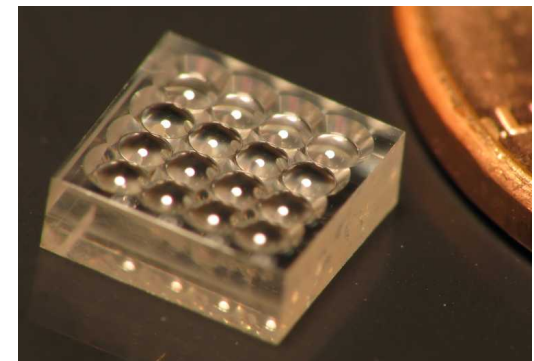


- 1x4 VCSEL arrays & 2x4 detector arrays attached to submount
 - parallel drive of VCSELs for low impedance
 - parallel connection of PDs to sum photocurrent signal
- Assemblies tested electrically prior to microlens integration

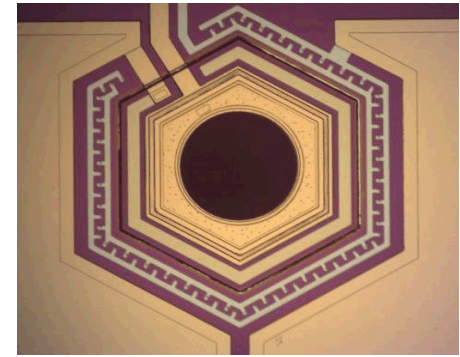
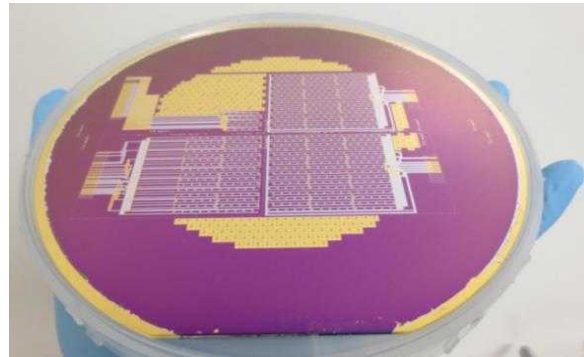
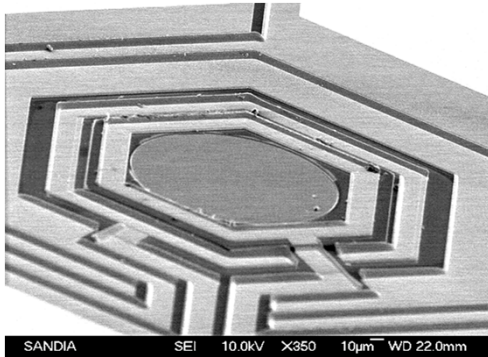
2x4 InGaAs photodiode array



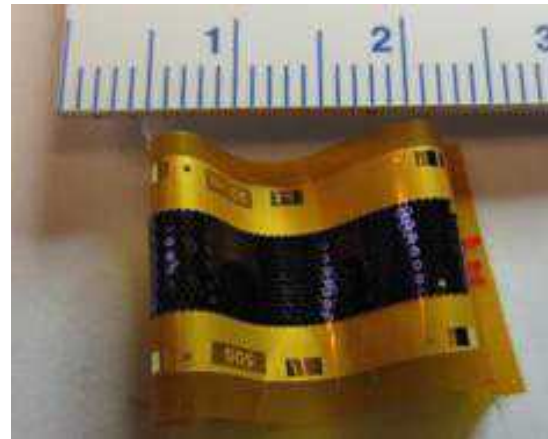
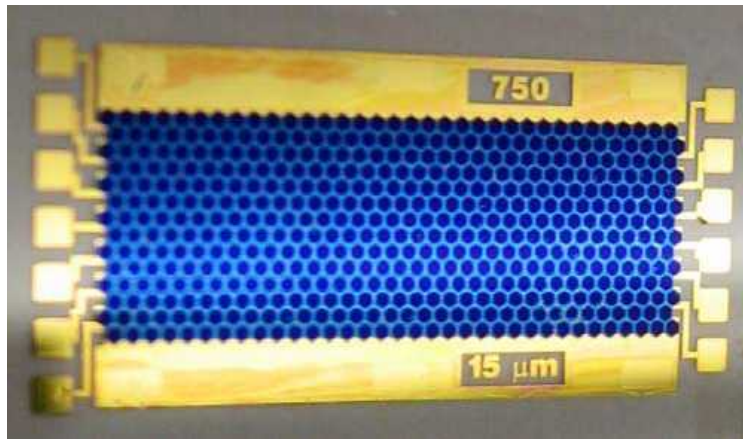
1x4 high-power VCSEL array
(980nm, bottom-emitting)



populated AlN fuse submount



InGaAsP/InP and InGaP/GaAs devices on silicon



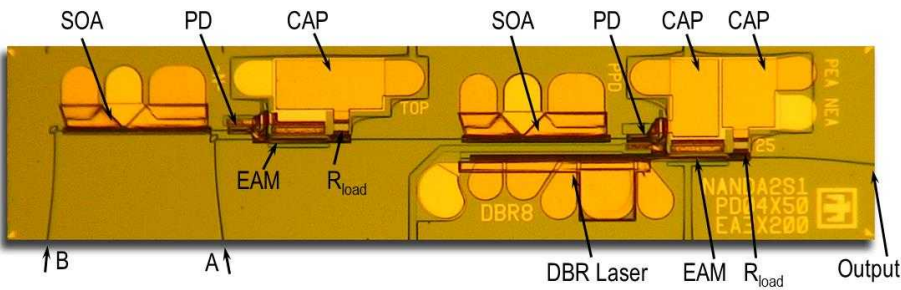
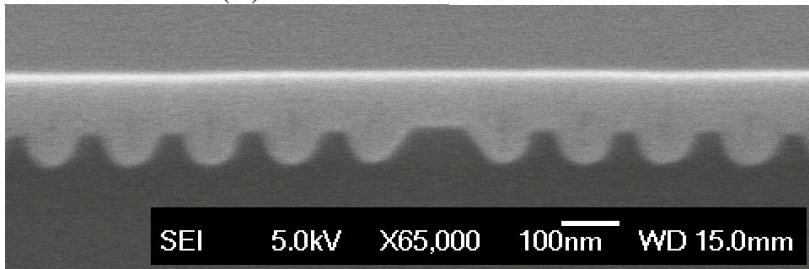
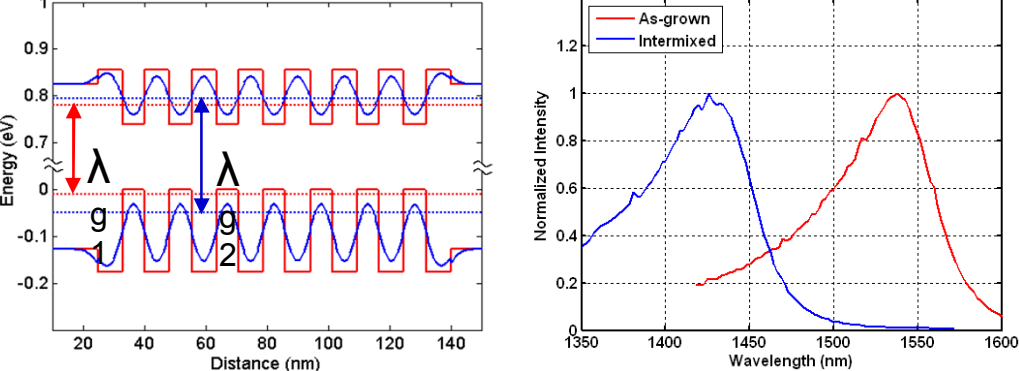
Flexible Substrates



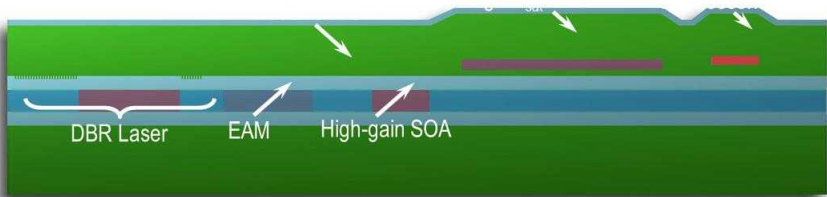
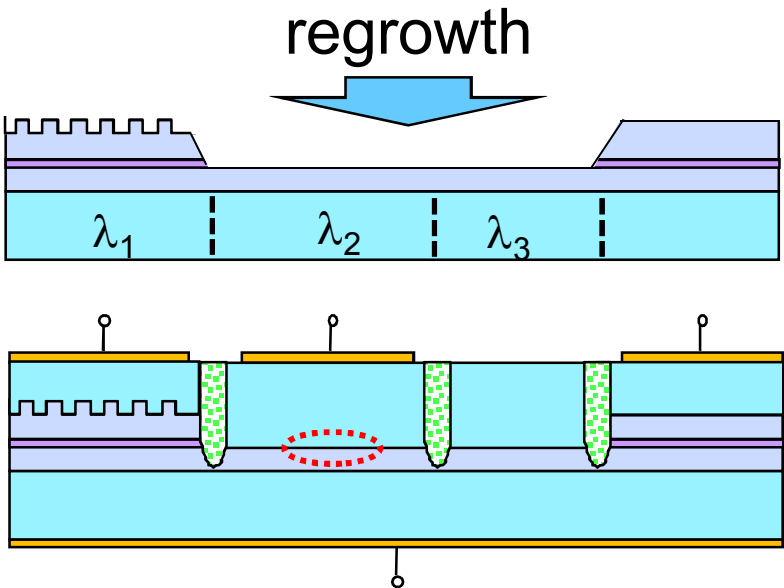
Collection Optics

Direct Growth for Integration – Photonic Integrated Circuits

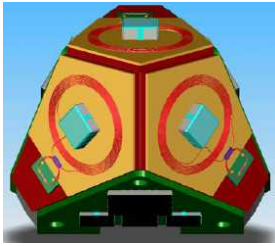
QWI



Top View of Photonic Integrated Circuit



Integrated PIC Assembly



- Competency and commitment in custom solutions for high reliability when industry is unable or unwilling to engage
- DOE supports National Lab involvement in strategy and project development for U.S. companies and universities with fairness of opportunity, without competing with industry, and with no organizational conflict of interest
- Decision to engage depends on unique value Sandia may contribute for enabling new understanding and securing a supply chain for national security applications

Sandia has a diverse array of technical expertise and co-located SMEs allowing us to

